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EE C247B - ME C218 Introduction to MEMS Design Spring 2019

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Lecture Module 6: Bulk Micromachining

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Lecture Outline

- Reading: Senturia Chpt. 3, Jaeger Chpt. 11, Handouts: "Bulk Micromachining of Silicon"
- Lecture Topics:
 - ↪ Bulk Micromachining
 - ↪ Anisotropic Etching of Silicon
 - ↪ Boron-Doped Etch Stop
 - ↪ Electrochemical Etch Stop
 - ↪ Isotropic Etching of Silicon
 - ↪ Deep Reactive Ion Etching (DRIE)

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Bulk Micromachining

- Basically, etching the substrate (usually silicon) to achieve microstructures
- Etching modes:
 - ↪ Isotropic vs. anisotropic
 - ↪ Reaction-limited
 - Etch rate dep. on temp.
 - ↪ Diffusion-limited
 - Etch rate dep. on mixing
 - Also dependent on layout & geometry, i.e., on loading
- Choose etch mode based on
 - ↪ Desired shape
 - ↪ Etch depth and uniformity
 - ↪ Surface roughness (e.g., sidewall roughness after etching)
 - ↪ Process compatibility (w/ existing layers)
 - ↪ Safety, cost, availability, environmental impact

	Wet etch	Plasma (dry) etch
Isotropic		
Anisotropic		

adsorption surface reaction desorption

slowest step controls rate of reaction


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Mechanical Properties of Silicon

- Crystalline silicon is a hard and brittle material that deforms elastically until it reaches its yield strength, at which point it breaks.
 - ↪ Tensile yield strength = 7 GPa (~1500 lb suspended from 1 mm²)
 - ↪ Young's Modulus near that of stainless steel
 - ↪ {100} = 130 GPa; {110} = 169 GPa; {111} = 188 GPa
 - ↪ Mechanical properties uniform, no intrinsic stress
 - ↪ Mechanical integrity up to 500°C
 - ↪ Good thermal conductor
 - ↪ Low thermal expansion coefficient
 - ↪ High piezoresistivity

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 **Anisotropic Wet Etching**

Anisotropic etches are available for single crystal Si:

- ↪ Orientation-dependent etching: $\langle 111 \rangle$ -plane more densely packed than $\langle 100 \rangle$ -plane

↑
Faster E.R. Slower E.R.

} ...in some solvents

↪ One such solvent: KOH + isopropyl alcohol
(e.g., 23.4 wt% KOH, 13.3 wt% isopropyl alcohol, 63 wt% H₂O)

⇒ $E.R._{\langle 100 \rangle} = 100 \times E.R._{\langle 111 \rangle}$